

Static Characteristics
T_J = 25°C unless otherwise specified
APT9F100B_S

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{BR(DSS)}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	1000			V
ΔV _{BR(DSS)} /ΔT _J	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D = 250μA		1.15		V/°C
R _{DS(on)}	Drain-Source On Resistance ^③	V _{GS} = 10V, I _D = 5A		1.28	1.6	Ω
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 1mA	2.5	4	5	V
ΔV _{GS(th)} /ΔT _J	Threshold Voltage Temperature Coefficient			-10		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 1000V V _{GS} = 0V			250 1000	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V			±100	nA

Dynamic Characteristics
T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g _{fs}	Forward Transconductance	V _{DS} = 50V, I _D = 5A		10.0		S
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V f = 1MHz		2606		pF
C _{rss}	Reverse Transfer Capacitance			35		
C _{oss}	Output Capacitance			219		
C _{o(cr)} ^④	Effective Output Capacitance, Charge Related	V _{GS} = 0V, V _{DS} = 0V to 670V		85		
C _{o(er)} ^⑤	Effective Output Capacitance, Energy Related			46		
Q _g	Total Gate Charge	V _{GS} = 0 to 10V, I _D = 5A, V _{DS} = 500V		80		nC
Q _{gs}	Gate-Source Charge			14		
Q _{gd}	Gate-Drain Charge			36		
t _{d(on)}	Turn-On Delay Time	Resistive Switching V _{DD} = 670V, I _D = 5A R _G = 10Ω ^⑥ , V _{GG} = 15V		25		ns
t _r	Current Rise Time			27		
t _{d(off)}	Turn-Off Delay Time			84		
t _f	Current Fall Time			24		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I _S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode)			9	A
I _{SM}	Pulsed Source Current (Body Diode) ^①				37	
V _{SD}	Diode Forward Voltage	I _{SD} = 5A, T _J = 25°C, V _{GS} = 0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} = 5A ^③ di _{SD} /dt = 100A/μs V _{DD} = 100V	T _J = 25°C	172	200	ns
			T _J = 125°C	286	345	
Q _{rr}	Reverse Recovery Charge		T _J = 25°C	.67		μC
			T _J = 125°C	1.5		
I _{rrm}	Reverse Recovery Current		T _J = 25°C	8		A
			T _J = 125°C	11		
dv/dt	Peak Recovery dv/dt	I _{SD} ≤ 5A, di/dt ≤ 1000A/μs, V _{DD} = 500V, T _J = 125°C			25	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at T_J = 25°C, L = 53mH, R_G = 25Ω, I_{AS} = 4A.

③ Pulse test: Pulse Width < 380μs, duty cycle < 2%.

④ C_{o(cr)} is defined as a fixed capacitance with the same stored charge as C_{OSS} with V_{DS} = 67% of V_{(BR)DSS}.

⑤ C_{o(er)} is defined as a fixed capacitance with the same stored energy as C_{OSS} with V_{DS} = 67% of V_{(BR)DSS}. To calculate C_{o(er)} for any value of V_{DS} less than V_{(BR)DSS}, use this equation: C_{o(er)} = -3.43E-8/V_{DS}² + 1.44E-8/V_{DS} + 5.38E-11.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

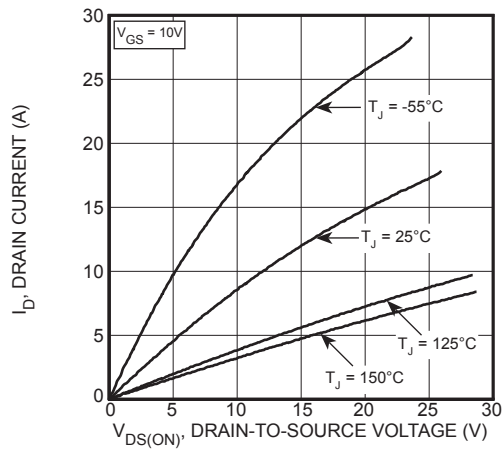


Figure 1, Output Characteristics

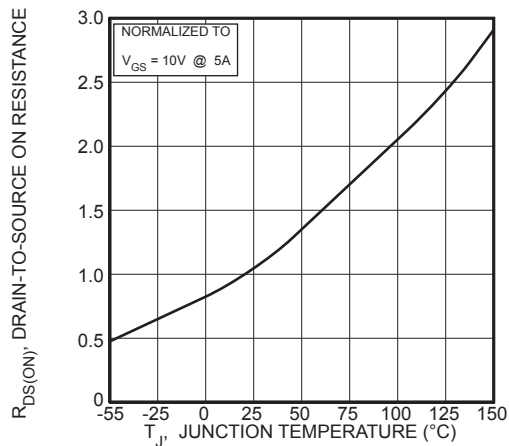
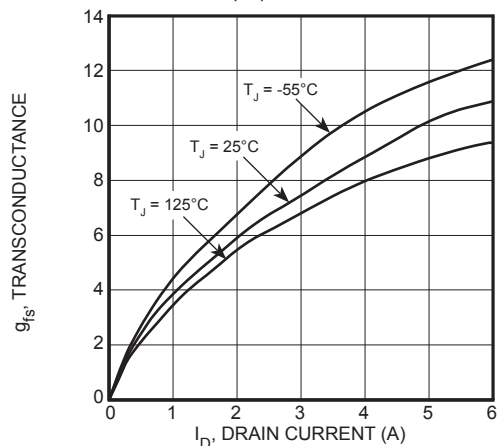
Figure 3, $R_{DS(ON)}$ vs Junction Temperature

Figure 5, Gain vs Drain Current

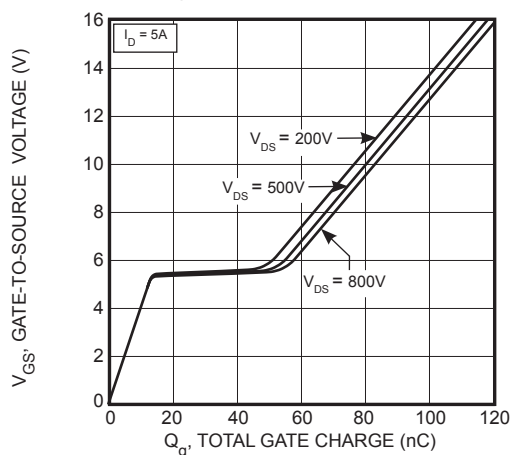


Figure 7, Gate Charge vs Gate-to-Source Voltage

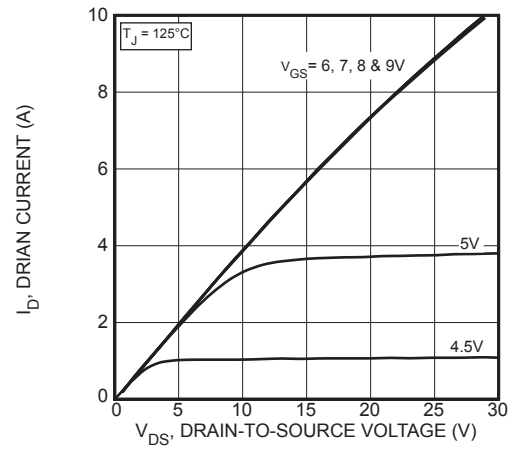


Figure 2, Output Characteristics

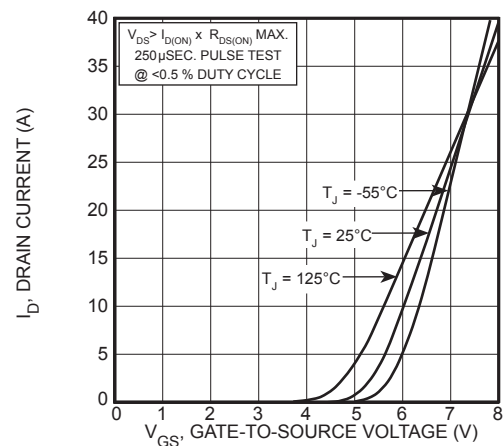


Figure 4, Transfer Characteristics

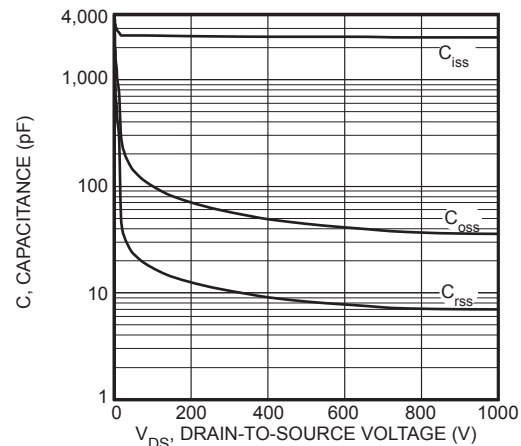


Figure 6, Capacitance vs Drain-to-Source Voltage

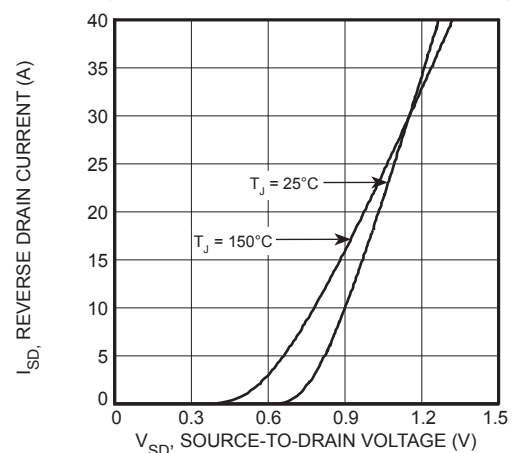


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

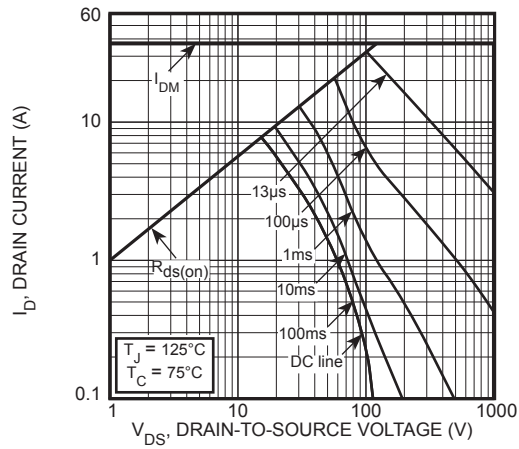


Figure 9, Forward Safe Operating Area

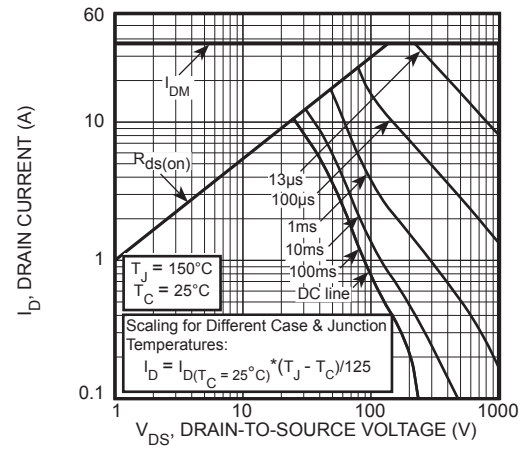


Figure 10, Maximum Forward Safe Operating Area

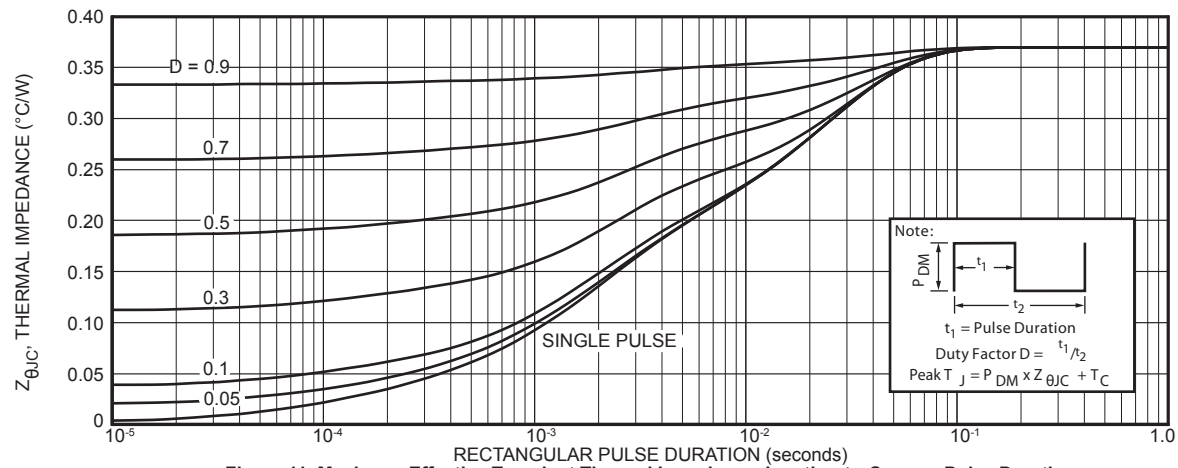
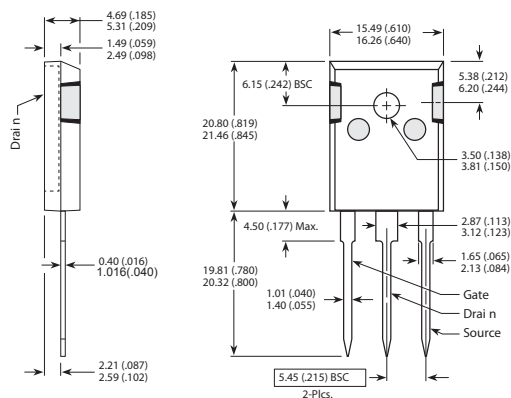


Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

TO-247 (B) Package Outline

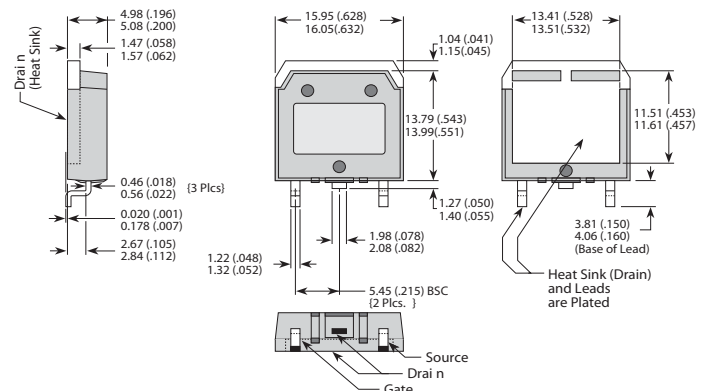
② SAC: Tin, Silver, Copper



Dimensions in Millimeters (Inches)

D³PAK Package Outline

③ 100% Sn Plated



Dimensions in Millimeters (Inches)